



Symbols and parameters				Values			Units
				min.	typ.	max.	
V_{RRM}	Repetitive peak reverse voltage	$T_j = 25^\circ\text{C}$			1700		V
I_F	Forward current (actual value)	$T_j = 175^\circ\text{C}$	$T_C = 25^\circ\text{C}$		953		A
			$T_C = 100^\circ\text{C}$		601		A
I_{FRM}	Repetitive peak forward current				1600		A
I_{FSM}	Surge forward current	10 ms	$T_j = 25^\circ\text{C}$		4160		A
			$T_j = 150^\circ\text{C}$		3712		A
i^2t	I^2t value, rating for fusing	10 ms	$T_j = 25^\circ\text{C}$		86528		A^2s
			$T_j = 150^\circ\text{C}$		68895		A^2s
V_F	Forward voltage	$I_F = 800$ A chipelevel	$T_j = 25^\circ\text{C}$		2.00	2.40	V
			$T_j = 150^\circ\text{C}$		2.15	2.57	V
V_{FO}	Forward threshold voltage	chipelevel	$T_j = 25^\circ\text{C}$		1.32	1.56	V
			$T_j = 150^\circ\text{C}$		1.08	1.22	V
r_F	On-state slope resistance, forward slope resistance	chipelevel	$T_j = 25^\circ\text{C}$		0.86	1.05	$\text{m}\Omega$
			$T_j = 150^\circ\text{C}$		1.34	1.69	$\text{m}\Omega$
I_R	Reverse current	$V_R = V_{RRM}$	$T_j = 25^\circ\text{C}$			0.68	mA
			$T_j = 150^\circ\text{C}$			200	mA
Q_{RR}	Reverse recovery charge	$I_F = 800$ A $di/dt_{\text{off}} = 4000$ A/ μs $V_R = 1200$ V	$T_j = 150^\circ\text{C}$		210		μC
I_{RRM}	Peak reverse recovery current		$T_j = 150^\circ\text{C}$		400		A
t_{rr}	Reverse recovery time		$T_j = 150^\circ\text{C}$		1.2		μs
E_{rr}	Energy dissipation during reverse recovery		$T_j = 150^\circ\text{C}$		140		mJ
$R_{th(j-c)}$	Thermal resistance, junction to case	per diode				0.58	K/W
$R_{th(c-s)}$	Thermal resistance, junction to heatsink	per diode/module ($\lambda_{\text{grease}} = 0.81$ W/ ($\text{m}\cdot\text{K}$))				0.045	K/W
		per diode/module, pre-applied phase change				-	K/W
L_{CE}	Parasitic collector-emitter inductance					15	nH
$R_{CC'+EE'}$	Resistance of the interconnections	measured per switch	$T_C = 25^\circ\text{C}$		0.23		$\text{m}\Omega$
			$T_C = 125^\circ\text{C}$		0.3		$\text{m}\Omega$
T_j	Junction temperature			-40		+175	$^\circ\text{C}$
T_{stg}	Storage temperature range			-40		+125	$^\circ\text{C}$
V_{isol}	Insulation test voltage (r.m.s.)	a.c. 50 Hz; r.m.s.;	1 s		4800		V
			1 min		4000		V
M_s	Mounting torque on heatsink			3		5	Nm
M_t	Mounting torque for terminals			2.5		5	Nm
a	Maximum allowable acceleration				$5 \cdot 9.81$		m/s^2
W	Weight				330		g

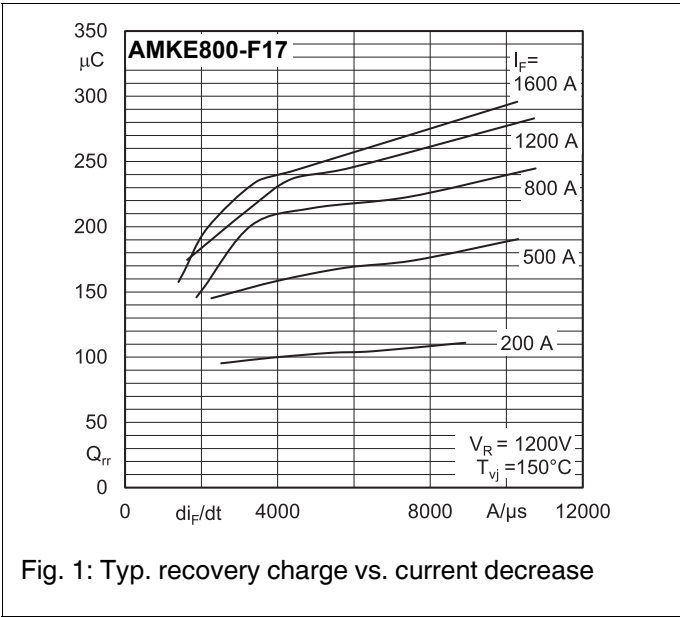


Fig. 1: Typ. recovery charge vs. current decrease

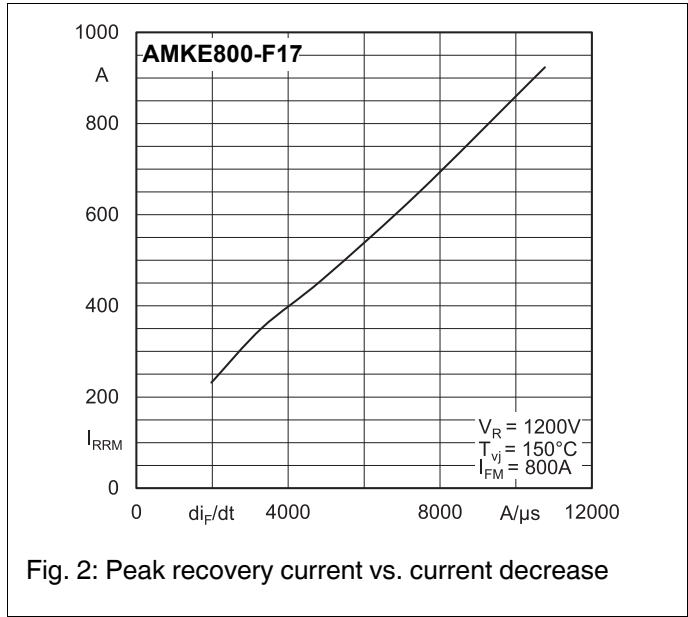


Fig. 2: Peak recovery current vs. current decrease

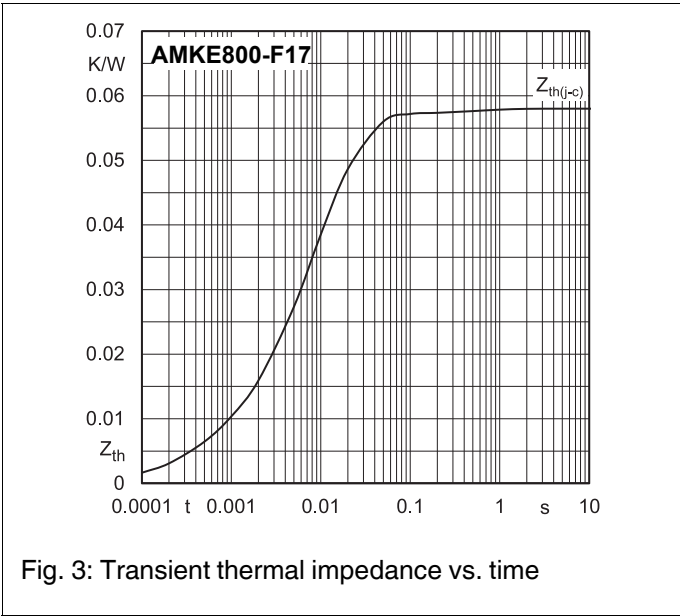


Fig. 3: Transient thermal impedance vs. time

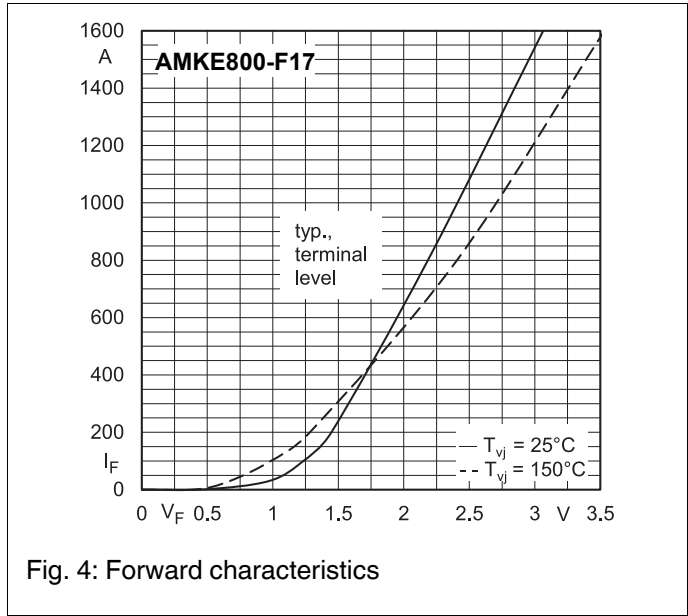


Fig. 4: Forward characteristics

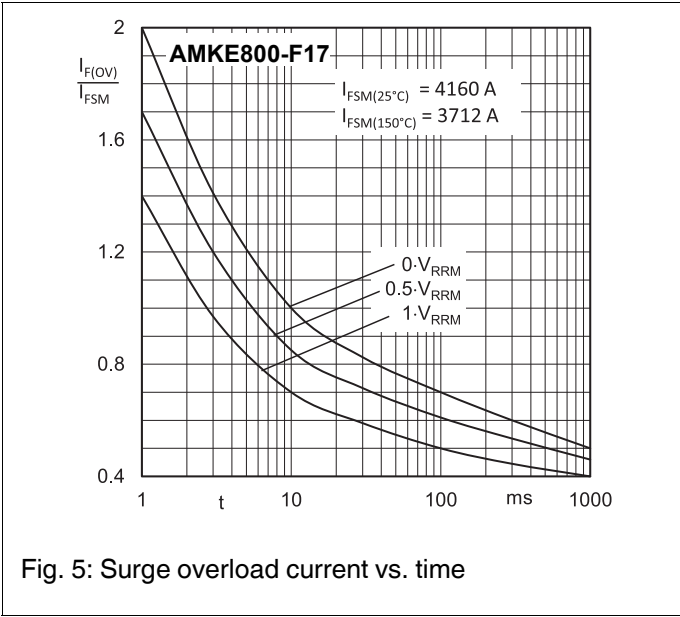


Fig. 5: Surge overload current vs. time

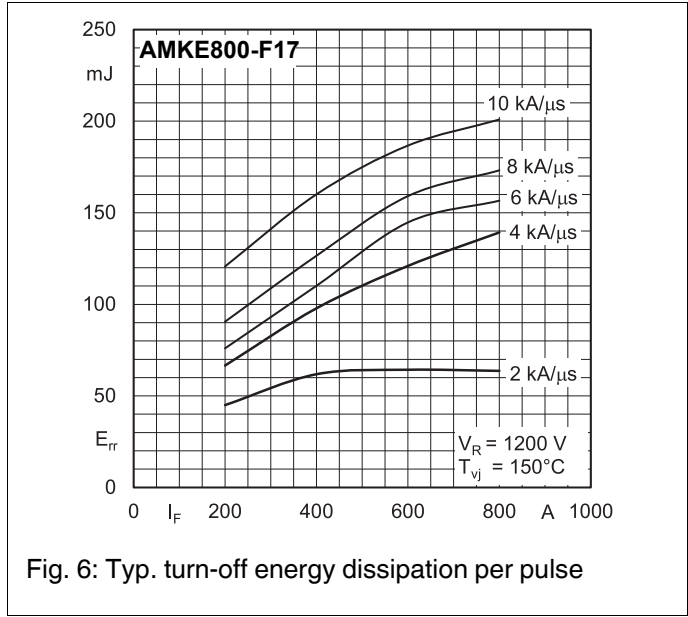
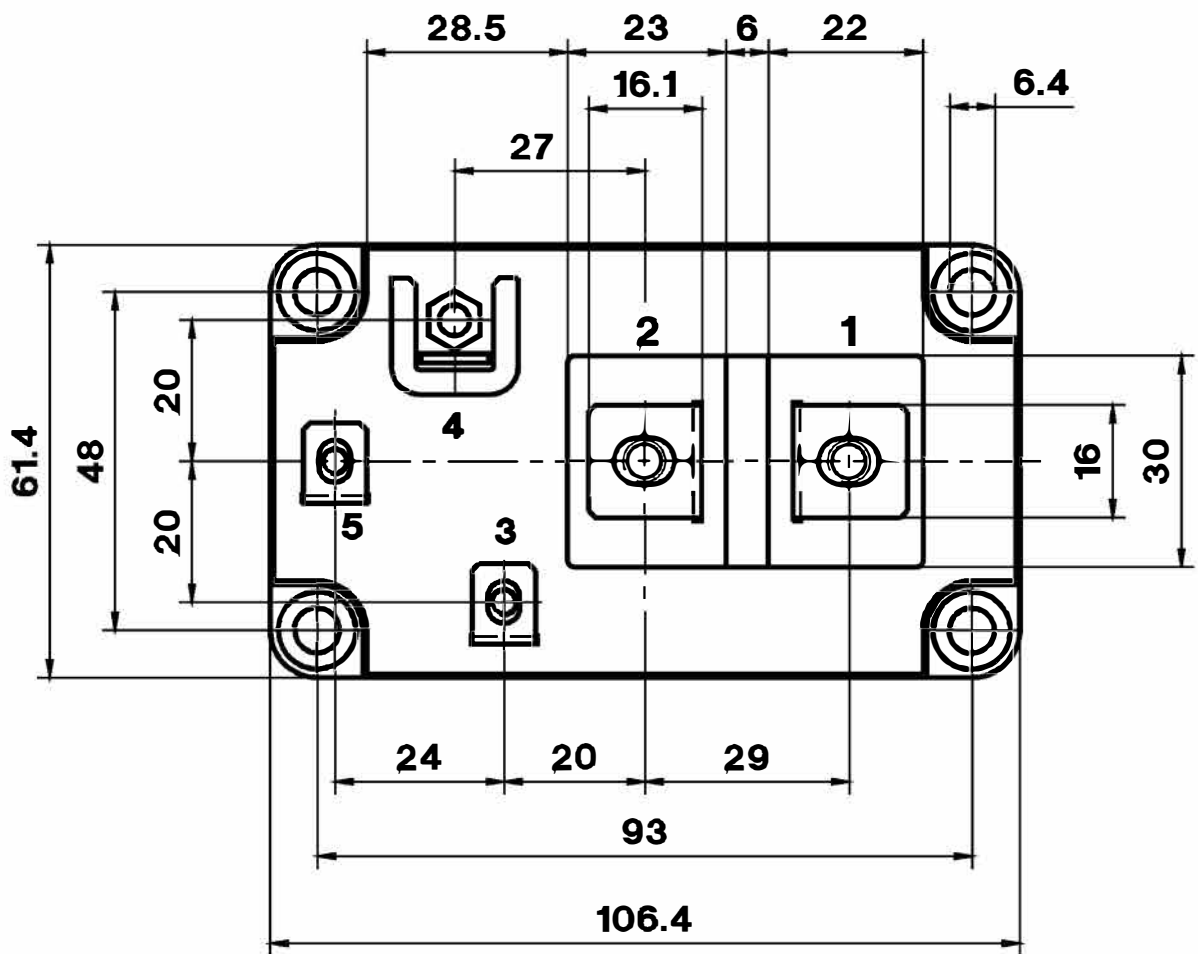
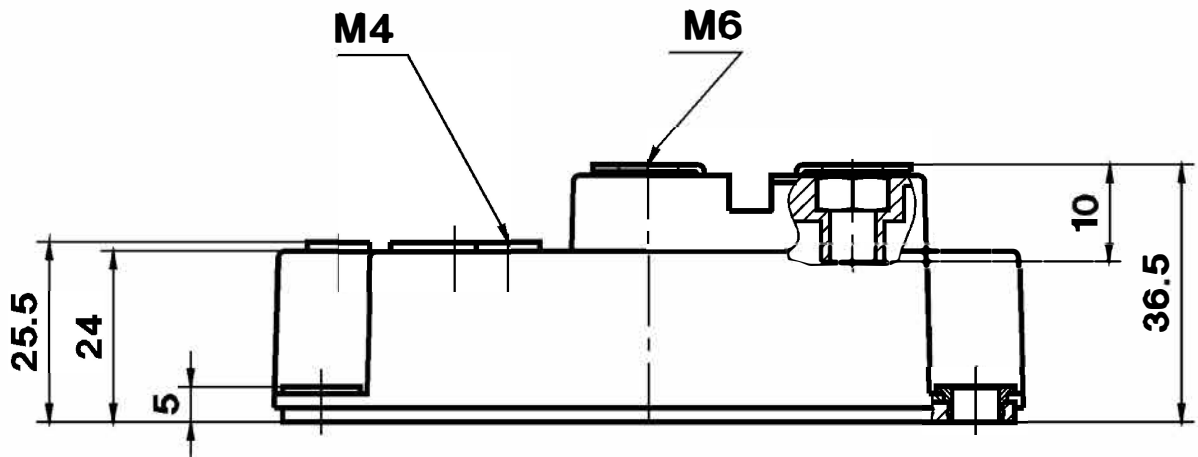


Fig. 6: Typ. turn-off energy dissipation per pulse

DIMENSIONS

CASED59



TOPOLOGY OF INTERNAL CONNECTION

